CY7C09159
CY7C09169

PRELIMINARY

8K/16K x 9
Synchronous Dual-Port Static RAM

Features

- **True Dual-Ported memory cells which allow simultaneous access of the same memory location**
- **2 Flow-Through/Pipelined devices**
  - **8K x 9 organization (CY7C09159)**
  - **16K x 9 organization (CY7C09169)**
- **3 Modes**
  - **Flow-Through**
  - **Pipelined**
  - **Burst**
- **Pipelined output mode on both ports allows fast 100-MHz cycle time**
- **0.35-micron CMOS for optimum speed/power**

- **High-speed clock to data access 6.5/7.5/12 ns (max.)**
- **Low operating power**
  - **Active= 200 mA (typical)**
  - **Standby= 0.05 mA (typical)**
- **Fully synchronous interface for easier operation**
- **Burst counters increment addresses internally**
  - **Shorten cycle times**
  - **Minimize bus noise**
  - **Supported in Flow-Through and Pipelined modes**
- **Dual Chip Enables for easy depth expansion**
- **Automatic power-down**
- **Commercial and Industrial temperature ranges**
- **Available in 100-pin TQFP**

Logic Block Diagram
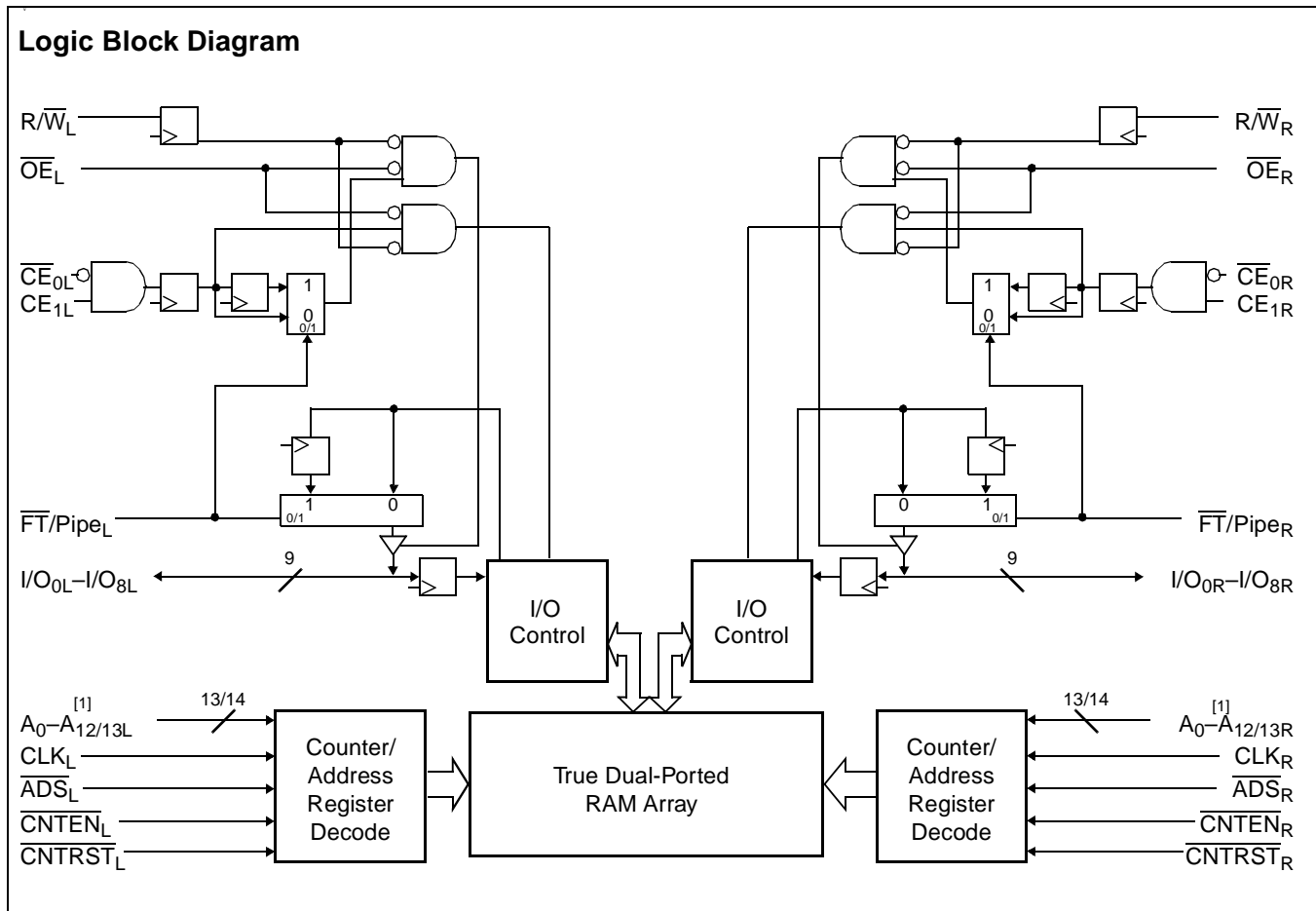
Note:

1. A_0–A_{12} for 8K; A_0–A_{13} for 16K.

For the most recent information, visit the Cypress web site at www.cypress.com

Functional Description

The CY7C09159 and CY7C09169 are high speed synchronous CMOS 8K and 16K x 9 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory.[2] Registers on control, address, and data lines allow for minimal set-up and hold times. In pipelined output mode, data is registered for decreased cycle time. Clock to data valid t_{CD2} = 6.5 ns (pipelined). Flow-through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow-through mode data will be available t_{CD1} = 15 ns after the address is clocked into the device. Pipelined output or flow-through mode is selected via the $\overline{FT}$/Pipe pin.

Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOW-to-HIGH transition of the clock signal. The internal write pulse is self-timed to allow the shortest possible cycle times.
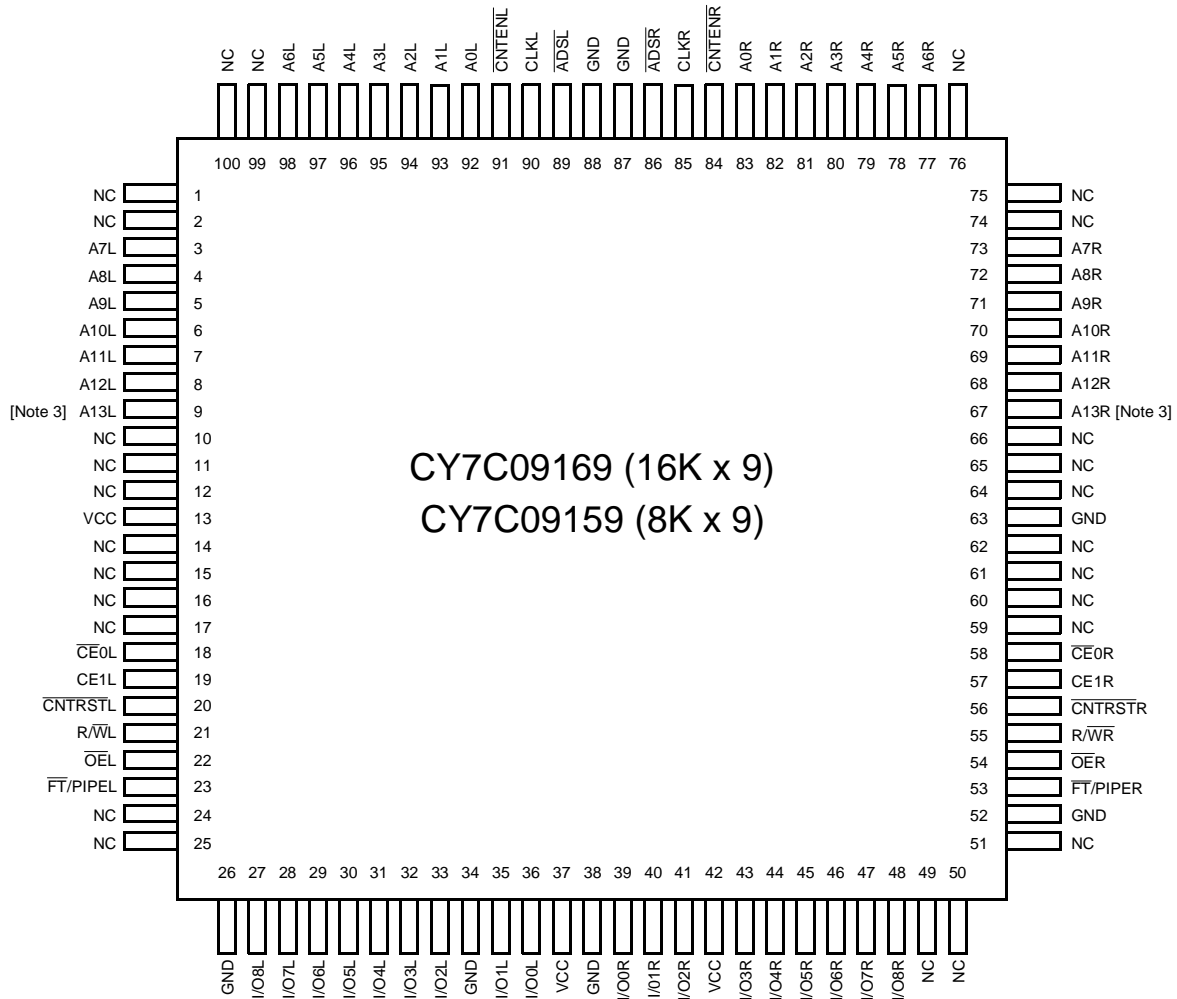
A HIGH on $\overline{CE}_0$ or LOW on CE_1 for one clock cycle will power down the internal circuitry to reduce the static power consumption. The use of multiple Chip Enables allows easier banking of multiple chips for depth expansion configurations. In the pipelined mode, one cycle is required with $\overline{CE}_0$ LOW and CE_1 HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and utilize the internal address generated by the internal counter for fast interleaved memory applications. A port's burst counter is loaded with the port's address strobe ($\overline{ADS}$). When the port's count enable ($\overline{CNTEN}$) is asserted, the address counter will increment on each LOW-to-HIGH transition of that port's clock signal. This will read/write one word from/into each successive address location until $\overline{CNTEN}$ is deasserted. The counter can address the entire memory array and will loop back to the start. Counter reset ($\overline{CNTRST}$) is used to reset the burst counter.

All parts are available in 100-pin Thin Quad Plastic Flatpack (TQFP) packages.

Note:
2. When simultaneously writing to the same location, final value cannot be guaranteed.

Pin Configurations

100-Pin TQFP
(Top View)

CY7C09169 (16K x 9)

CY7C09159 (8K x 9)

Top row (pins 100–76): NC, NC, A6L, A5L, A4L, A3L, A2L, A1L, A0L, $\overline{\text{CNTEN}}$L, CLKL, $\overline{\text{ADS}}$L, GND, GND, $\overline{\text{ADS}}$R, CLKR, $\overline{\text{CNTEN}}$R, A0R, A1R, A2R, A3R, A4R, A5R, A6R, NC

Left column (pins 1–25):
Pin	Name
1	NC
2	NC
3	A7L
4	A8L
5	A9L
6	A10L
7	A11L
8	A12L
9	A13L [Note 3]
10	NC
11	NC
12	NC
13	VCC
14	NC
15	NC
16	NC
17	NC
18	$\overline{\text{CE0}}$L
19	CE1L
20	$\overline{\text{CNTRST}}$L
21	R/$\overline{\text{W}}$L
22	$\overline{\text{OE}}$L
23	$\overline{\text{FT}}$/PIPEL
24	NC
25	NC

Right column (pins 75–51):
Pin	Name
75	NC
74	NC
73	A7R
72	A8R
71	A9R
70	A10R
69	A11R
68	A12R
67	A13R [Note 3]
66	NC
65	NC
64	NC
63	GND
62	NC
61	NC
60	NC
59	NC
58	$\overline{\text{CE0}}$R
57	CE1R
56	$\overline{\text{CNTRST}}$R
55	R/$\overline{\text{W}}$R
54	$\overline{\text{OE}}$R
53	$\overline{\text{FT}}$/PIPER
52	GND
51	NC

Bottom row (pins 26–50): GND, I/O8L, I/O7L, I/O6L, I/O5L, I/O4L, I/O3L, I/O2L, GND, I/O1L, I/O0L, VCC, GND, I/O0R, I/O1R, I/O2R, VCC, I/O3R, I/O4R, I/O5R, I/O6R, I/O7R, I/O8R, NC, NC

Note:
3. This pin is NC for CY7C09159.

Selection Guide

	CY7C09159 CY7C09169 -6	CY7C09159 CY7C09169 -7	CY7C09159 CY7C09169 -12
f_{MAX2} (MHz) (Pipelined)	100	83	50
Max Access Time (ns) (Clock to Data, Pipelined)	6.5	7.5	12
Typical Operating Current I_{CC} (mA)	250	235	195
Typical Standby Current for I_{SB1} (mA) (Both Ports TTL Level)	45	40	30
Typical Standby Current for I_{SB3} (mA) (Both Ports CMOS Level)	0.05	0.05	0.05

Pin Definitions

Left Port	Right Port	Description
A_{0L}–A_{13L}	A_{0R}–A_{13R}	Address Inputs. (A_0–A_{12} for 8K; A_0–A_{13} for 16K devices)
$\overline{ADS}_L$	$\overline{ADS}_R$	Address Strobe Input. Used as an address qualifier. This signal should be asserted LOW during normal read or write transactions. Asserting this signal LOW also loads the burst address counter with data present on the I/O pins.
$\overline{CE}_{0L}$,CE_{1L}	$\overline{CE}_{0R}$,CE_{1R}	Chip Enable Input. To select either the left or right port, both $\overline{CE}_0$ AND CE_1 must be asserted to their active states ($\overline{CE}_0 \leq V_{IL}$ and $CE_1 \geq V_{IH}$).
CLK_L	CLK_R	Clock Signal. This input can be free running or strobed. Maximum clock input rate is f_{MAX}.
$\overline{CNTEN}_L$	$\overline{CNTEN}_R$	Counter Enable Input. Asserting this signal LOW increments the burst address counter of its respective port on each rising edge of CLK. $\overline{CNTEN}$ is disabled if $\overline{ADS}$ or $\overline{CNTRST}$ are asserted LOW.
$\overline{CNTRST}_L$	$\overline{CNTRST}_R$	Counter Reset Input. Asserting this signal LOW resets the burst address counter of its respective port to zero. $\overline{CNTRST}$ is not disabled by asserting $\overline{ADS}$ or $\overline{CNTEN}$.
I/O_{0L}–I/O_{8L}	I/O_{0R}–I/O_{8R}	Data Bus Input/Output (I/O_0–I/O_7 for x8 devices; I/O_0–I/O_8 for x9 devices).
$\overline{OE}_L$	$\overline{OE}_R$	Output Enable Input. This signal must be asserted LOW to enable the I/O data pins during read operations.
$R/\overline{W}_L$	$R/\overline{W}_R$	Read/Write Enable Input. This signal is asserted LOW to write to the dual port memory array. For read operations, assert this pin HIGH.
$\overline{FT}/PIPE_L$	$\overline{FT}/PIPE_R$	Flow-Through/Pipelined Select Input. For flow-through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.
GND		Ground Input.
NC		No Connect.
V_{CC}		Power Input.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .... $-65°C$ to $+150°C$

Ambient Temperature with Power Applied ..$-55°C$ to $+125°C$

Supply Voltage to Ground Potential .... $-0.3V$ to $+7.0V$

DC Voltage Applied to
Outputs in High Z State .... $-0.5V$ to $+7.0V$

DC Input Voltage.. $-0.5V$ to $+7.0V$

Output Current into Outputs (LOW)............................ 20 mA

Static Discharge Voltage .... >2001V

Latch-Up Current.. >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	$0°C$ to $+70°C$	$5V \pm 10\%$
Industrial	$-40°C$ to $+85°C$	$5V \pm 10\%$

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Electrical Characteristics Over the Operating Range

Symbol	Parameter		CY7C09159 CY7C09169									Units
			-6			-7			-12			
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OH}	Output HIGH Voltage (V_{CC}=Min, I_{OH}=−4.0 mA)		2.4			2.4			2.4			V
V_{OL}	Output LOW Voltage (V_{CC}=Min, I_{OH}= +4.0 mA)				0.4			0.4			0.4	V
V_{IH}	Input HIGH Voltage		2.2			2.2			2.2			V
V_{IL}	Input LOW Voltage				0.8			0.8			0.8	V
I_{OZ}	Output Leakage Current		−10		10	−10		10	−10		10	μA
I_{CC}	Operating Current (V_{CC}=Max, I_{OUT}=0 mA) Outputs Disabled	Com'l.		250	450		235	420		195	300	mA
		Indust.					260	445		225	375	mA
I_{SB1}	Standby Current (Both Ports TTL Level)[4] $\overline{CE}_L$ & $\overline{CE}_R \geq V_{IH}$, f=$f_{MAX}$	Com'l.		45	115		40	105		30	85	mA
		Indust.					55	120		45	100	mA
I_{SB2}	Standby Current (One Port TTL Level)[4] $\overline{CE}_L$	$\overline{CE}_R \geq V_{IH}$, f=$f_{MAX}$	Com'l.		175	235		160	220		125	190	mA
		Indust.					175	235		140	205	mA
I_{SB3}	Standby Current (Both Ports CMOS Level)[4] $\overline{CE}_L$ & $\overline{CE}_R \geq V_{CC} - 0.2V$, f=0	Com'l.		0.05	0.25		0.05	0.25		0.05	0.25	mA
		Indust.					0.05	0.25		0.05	0.25	mA
I_{SB4}	Standby Current (One Port CMOS Level)[4] $\overline{CE}_L$	$\overline{CE}_R \geq V_{IH}$, f=$f_{MAX}$	Com'l.		160	200		145	185		110	150	mA
		Indust.					160	200		125	165	mA

Capacitance

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^oC$, f = 1 MHz, $V_{CC} = 5.0V$	10	pF
C_{OUT}	Output Capacitance		10	pF

AC Test Loads
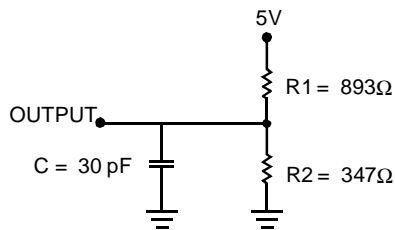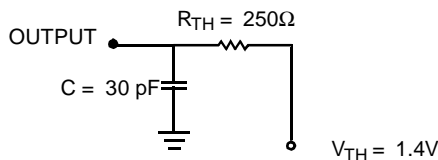
(a) Normal Load (Load 1)   **(b) Thévenin Equivalent (Load 1)**   **(c) Three-State Delay (Load 2)**
(Used for t_{CKLZ}, t_{OLZ}, & t_{OHZ} including scope and jig)
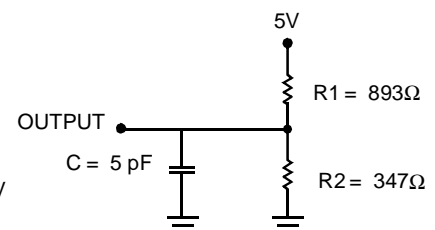
ALL INPUT PULSES
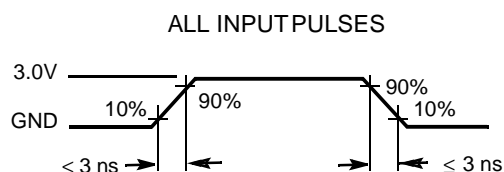
Note:
4. $\overline{CE}_L$ and $\overline{CE}_R$ are internal signals. To select either the left or right port, both $\overline{CE}_0$ AND CE_1 must be asserted to their active states ($\overline{CE}_0 \leq V_{IL}$ and $CE_1 \geq V_{IH}$).

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Switching Characteristics Over the Operating Range

| Symbol | Parameter | CY7C09159 CY7C09169 | | | | | | Units |
| | | -6 | | -7 | | -12 | | |
		Min	Max	Min	Max	Min	Max	
f_{MAX1}	f_{Max} Flow-Through		53		45		33	MHz
f_{MAX2}	f_{Max} Pipelined		100		83		50	MHz
t_{CYC1}	Clock Cycle Time - Flow-Through	19		22		30		ns
t_{CYC2}	Clock Cycle Time - Pipelined	10		12		20		ns
t_{CH1}	Clock HIGH Time - Flow-Through	6.5		7.5		12		ns
t_{CL1}	Clock LOW Time - Flow-Through	6.5		7.5		12		ns
t_{CH2}	Clock HIGH Time - Pipelined	4		5		8		ns
t_{CL2}	Clock LOW Time - Pipelined	4		5		8		ns
t_R	Clock Rise Time		3		3		3	ns
t_F	Clock Fall Time		3		3		3	ns
t_{SA}	Address Set-up Time	3.5		4		4		ns
t_{HA}	Address Hold Time	0		0		1		ns
t_{SC}	Chip Enable Set-up Time	3.5		4		4		ns
t_{HC}	Chip Enable Hold Time	0		0		1		ns
t_{SW}	R/$\overline{W}$ Set-up Time	3.5		4		4		ns
t_{HW}	R/$\overline{W}$ Hold Time	0		0		1		ns
t_{SD}	Input Data Set-up Time	3.5		4		4		ns
t_{HD}	Input Data Hold Time	0		0		1		ns
t_{SAD}	$\overline{ADS}$ Set-up Time	3.5		4		4		ns
t_{HAD}	$\overline{ADS}$ Hold Time	0		0		1		ns
t_{SCN}	$\overline{CNTEN}$ Set-up Time	3.5		4		4		ns
t_{HCN}	$\overline{CNTEN}$ Hold Time	0		0		1		ns
t_{SRST}	$\overline{CNTRST}$ Set-up Time	3.5		4		4		ns
t_{HRST}	$\overline{CNTRST}$ Hold Time	0		0		1		ns
t_{OE}	Output Enable to Data Valid		8		9		12	ns
t_{OLZ}	$\overline{OE}$ to Low Z	2		2		2		ns
t_{OHZ}	$\overline{OE}$ to High Z	1	7	1	7	1	7	ns
t_{CD1}	Clock to Data Valid - Flow-Through		15		18		25	ns
t_{CD2}	Clock to Data Valid - Pipelined		6.5		7.5		12	ns
t_{DC}	Data Output Hold After Clock HIGH	2		2		2		ns
t_{CKHZ}	Clock HIGH to Output High Z	2	9	2	9	2	9	ns
t_{CKLZ}	Clock HIGH to Output Low Z	2		2		2		ns
Port to Port Delays								
t_{CWDD}	Write Port Clock HIGH to Read Data Delay		30		35		40	ns
t_{CCS}	Clock to Clock Set-up Time		9		10		15	ns

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Switching Waveforms

Read Cycle for Flow-Through Output ($\overline{FT}$/PIPE = V_{IL})[5,6,7,8]
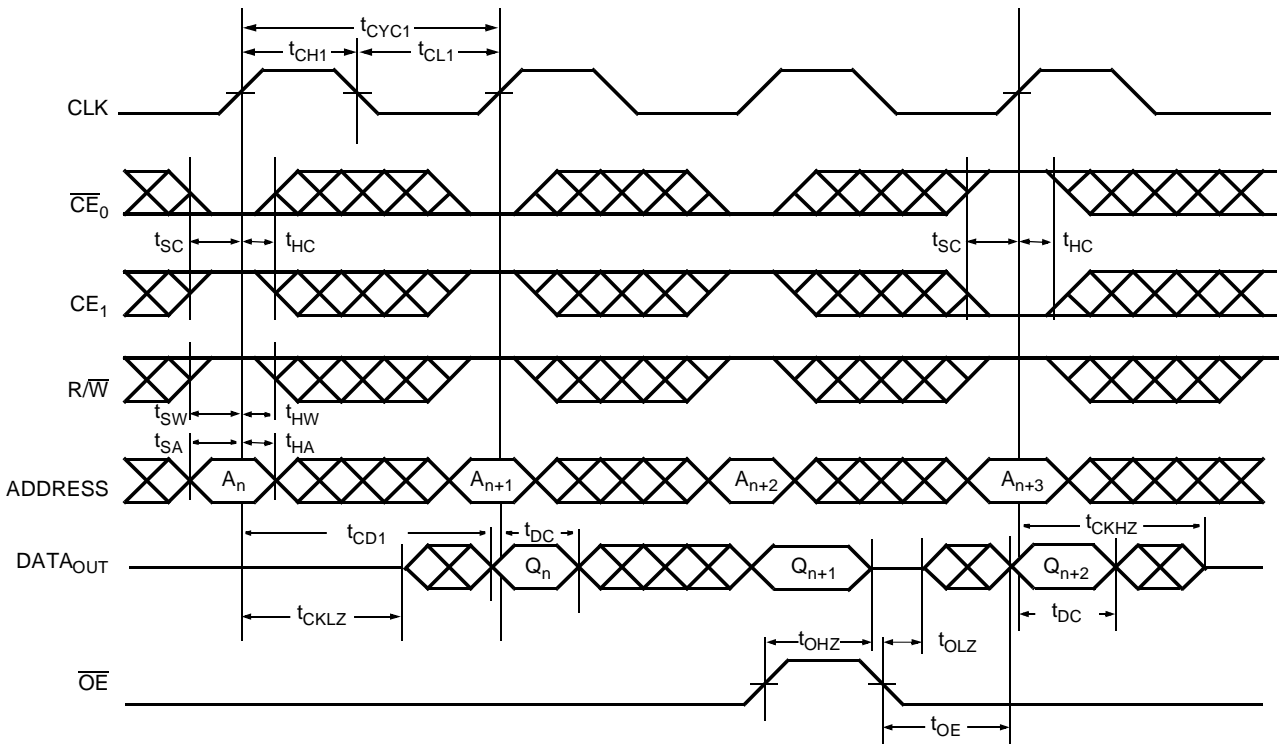
Read Cycle for Pipelined Operation ($\overline{FT}$/PIPE = V_{IH})[5,6,7,8]
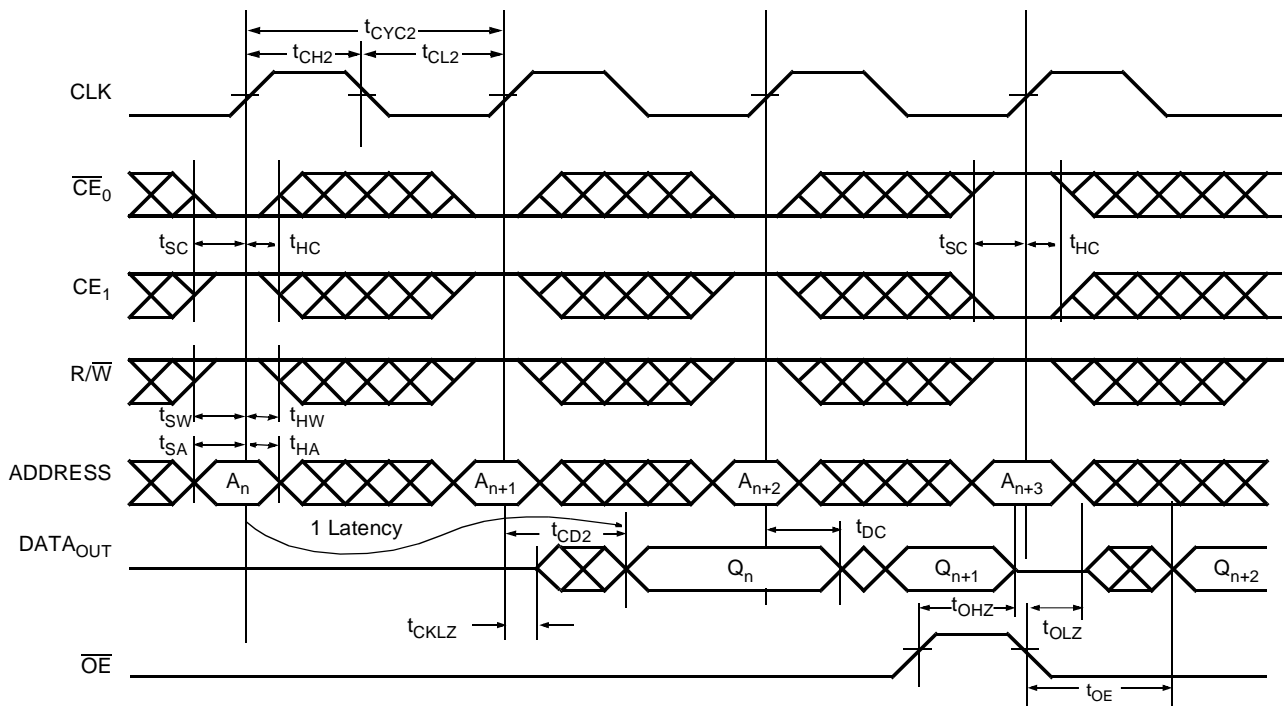
Notes:
5. $\overline{OE}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
6. $\overline{ADS}$ = V_{IL}, $\overline{CNTEN}$ and $\overline{CNTRST}$ = V_{IH}.
7. The output is disabled (high-impedance state) by $\overline{CE}_0 = V_{IH}$ or CE_1 = V_{IL} following the next rising edge of the clock.
8. Addresses do not have to be accessed sequentially since $\overline{ADS}$ = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

Switching Waveforms (continued)
Bank Select Pipelined Read[9,10]
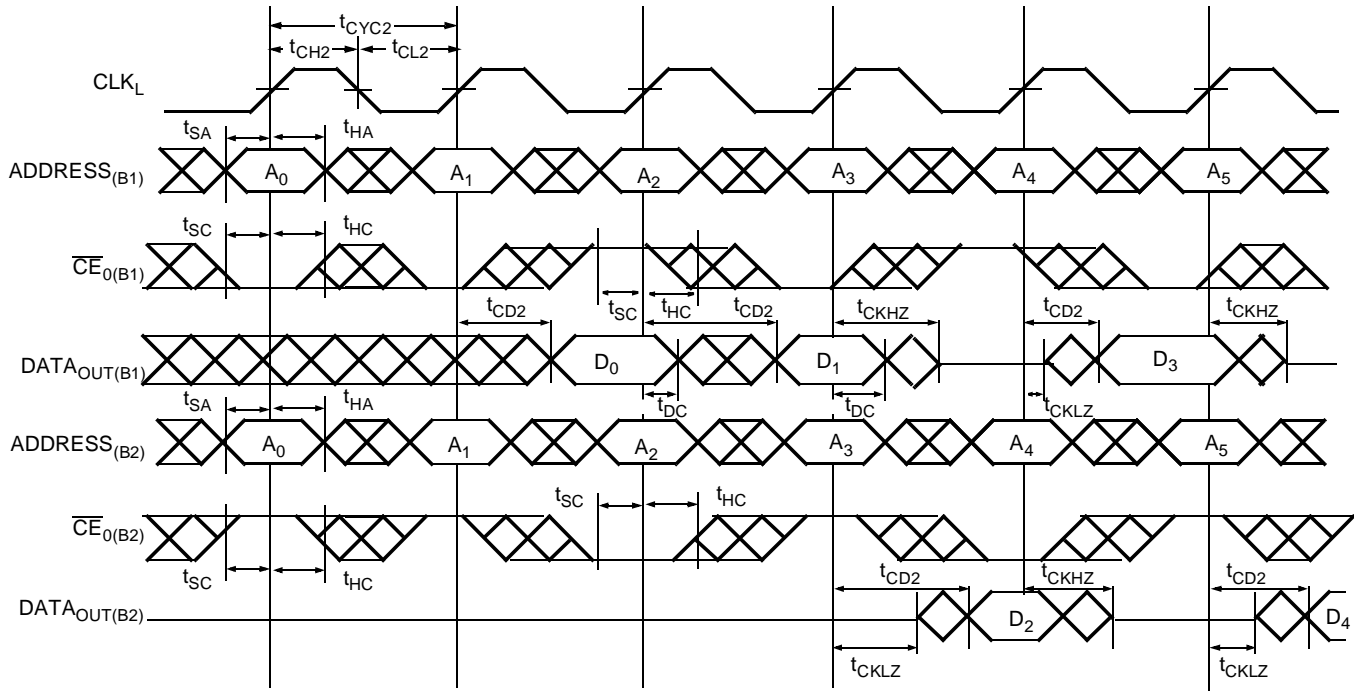
Left Port Write to Flow-Through Right Port Read[11,12,13,14]
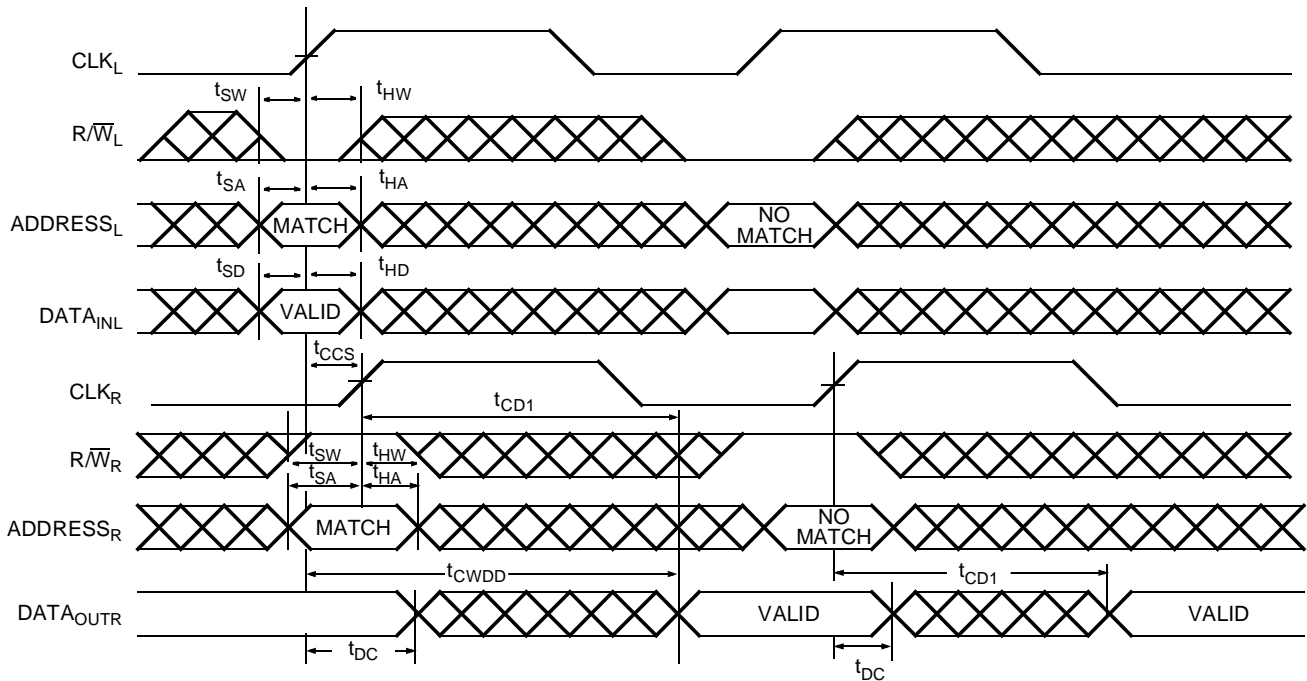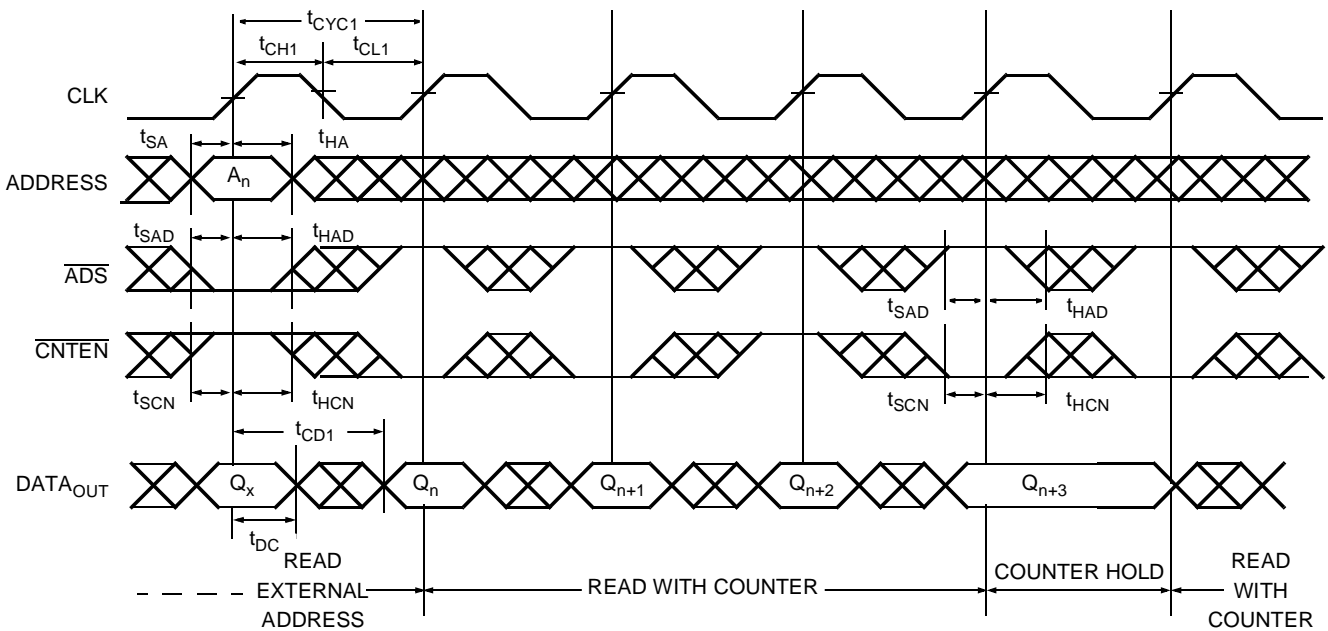

Notes:
9. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2. Each Bank consists of one Cypress dual-port device from this datasheet.
   $ADDRESS_{(B1)} = ADDRESS_{(B2)}$.
10. $\overline{OE}$ and $\overline{ADS} = V_{IL}$; $CE_{1(B1)}$, $CE_{1(B2)}$, $R/\overline{W}$, $\overline{CNTEN}$, and $\overline{CNTRST} = V_{IH}$.
11. The same waveforms apply for a right port write to flow-through left port read.
12. $\overline{CE}_0$ and $\overline{ADS} = V_{IL}$; CE_1, $\overline{CNTEN}$, and $\overline{CNTRST} = V_{IH}$.
13. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
14. It $t_{CCS} \leq$ maximum specified, then data from right port READ is not valid until the maximum specified for t_{CWDD}. If $t_{CCS}>$maximum specified, then data is not valid until $t_{CCS} + t_{CD1}$. t_{CWDD} does not apply in this case.
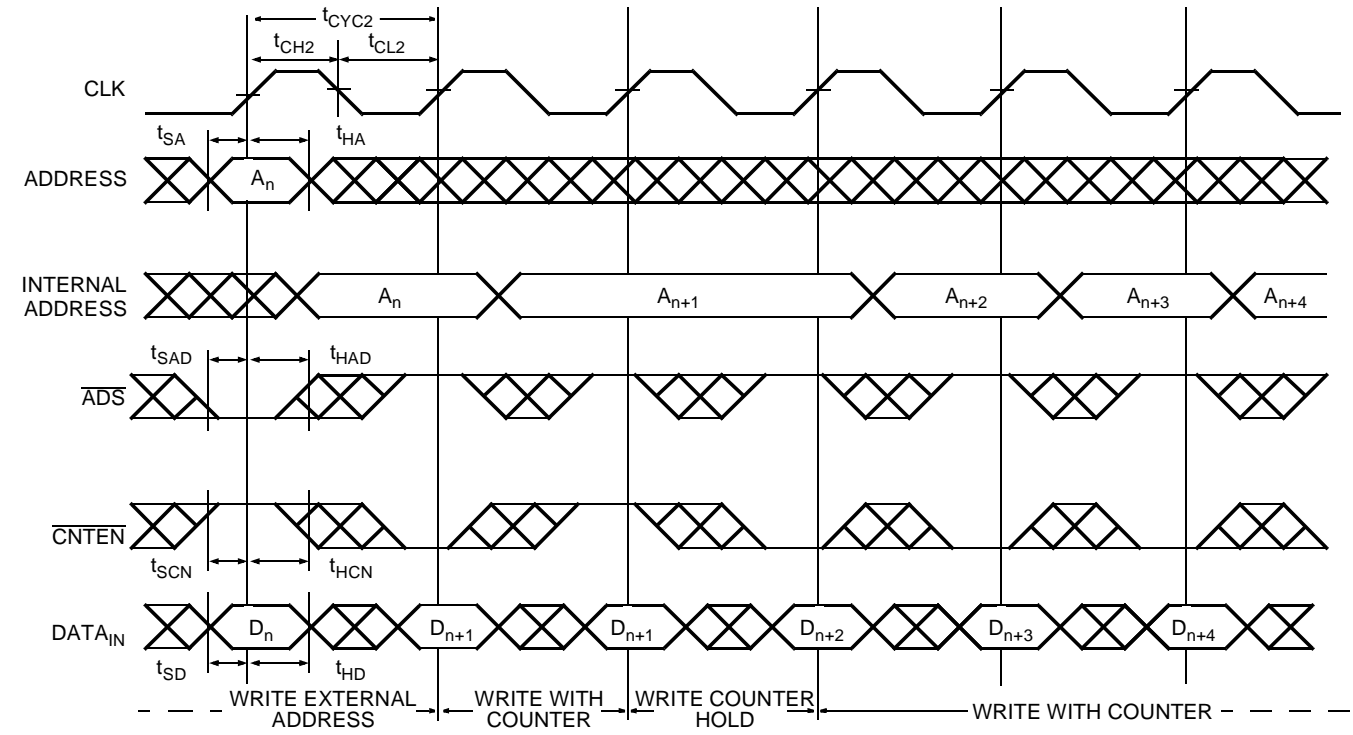
PRELIMINARY

Switching Waveforms (continued)

Pipelined Read-to-Write-to-Read ($\overline{OE}$ = V_{IL})[8,12,15,16]
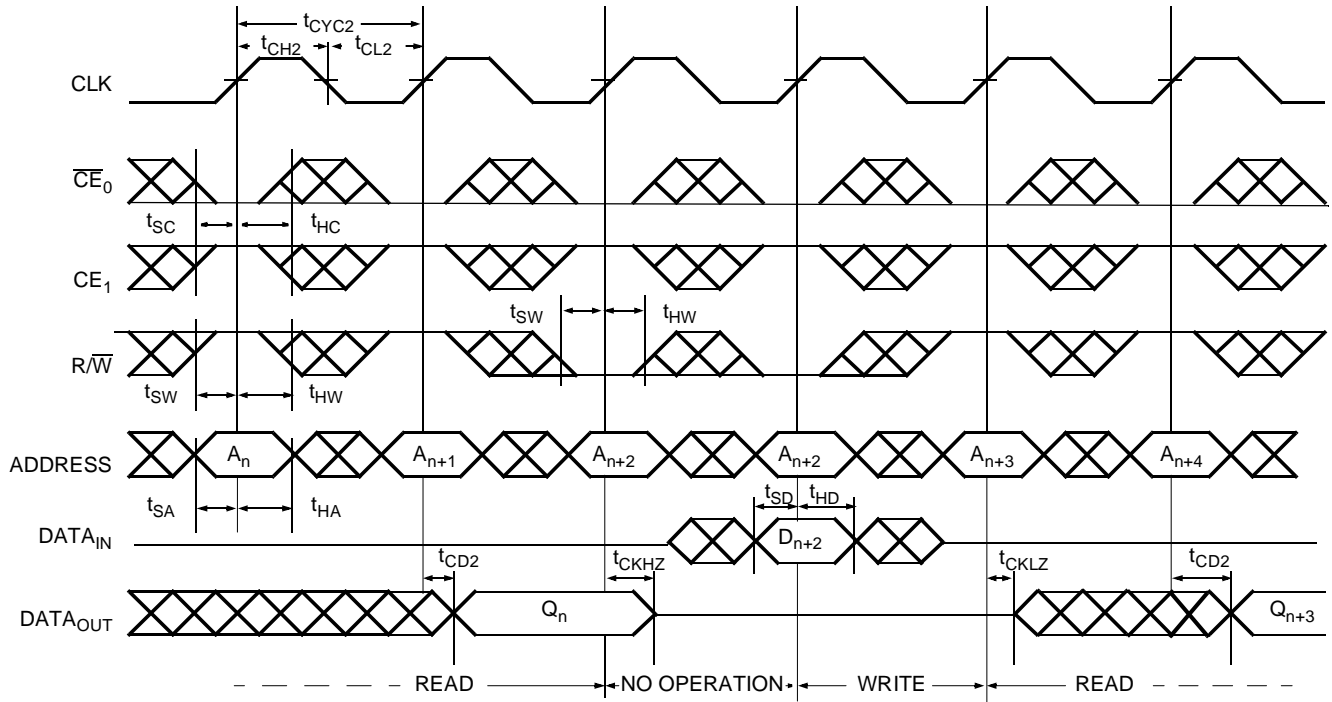
Pipelined Read-to-Write-to-Read ($\overline{OE}$ Controlled)[8,12,15,16]
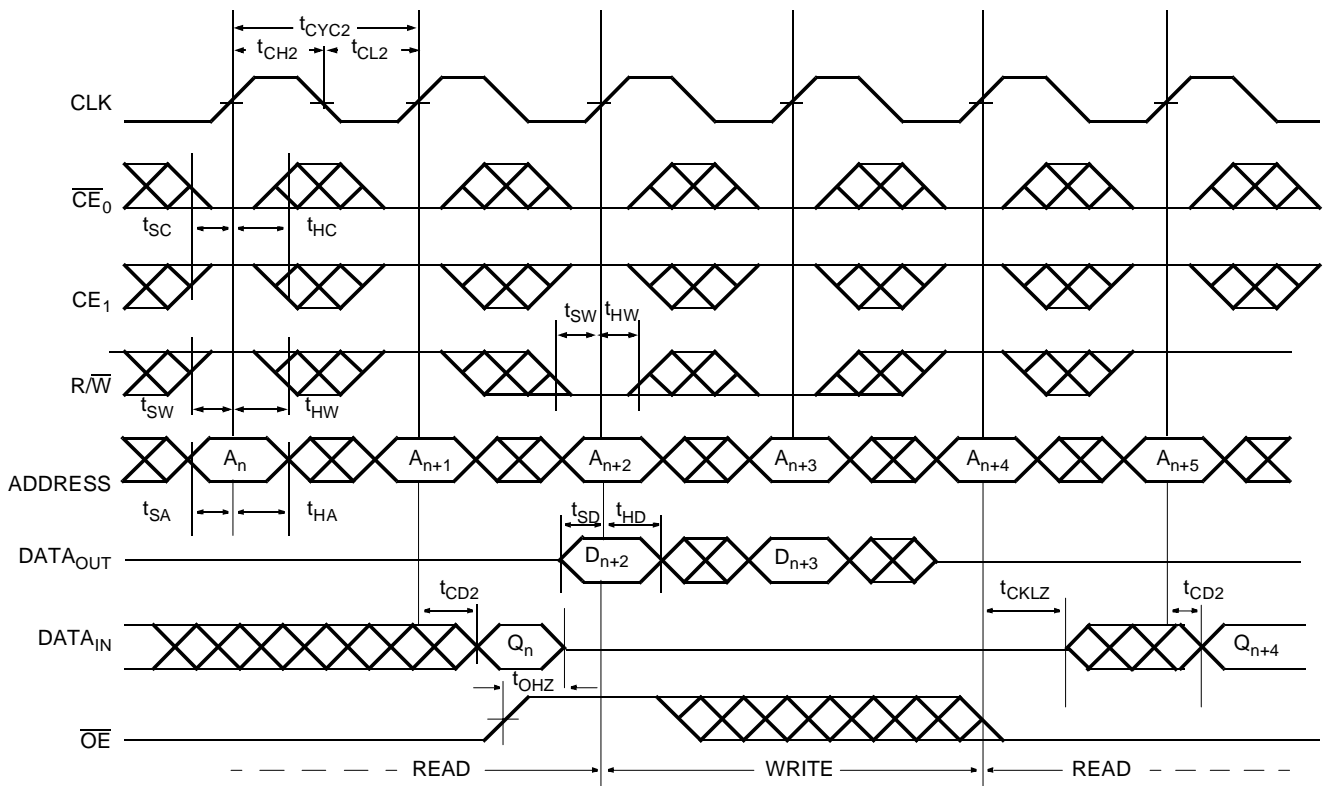
Notes:
15. Output state (HIGH, LOW, or High-Impedance) is determined by the previous cycle control signals.
16. During "No operation", data in memory at the selected address may be corrupted and should be re-written to ensure data integrity.

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Switching Waveforms (continued)

Flow-Through Read-to-Write-to-Read ($\overline{OE}$ = V_{IL})[6,8,12,15]
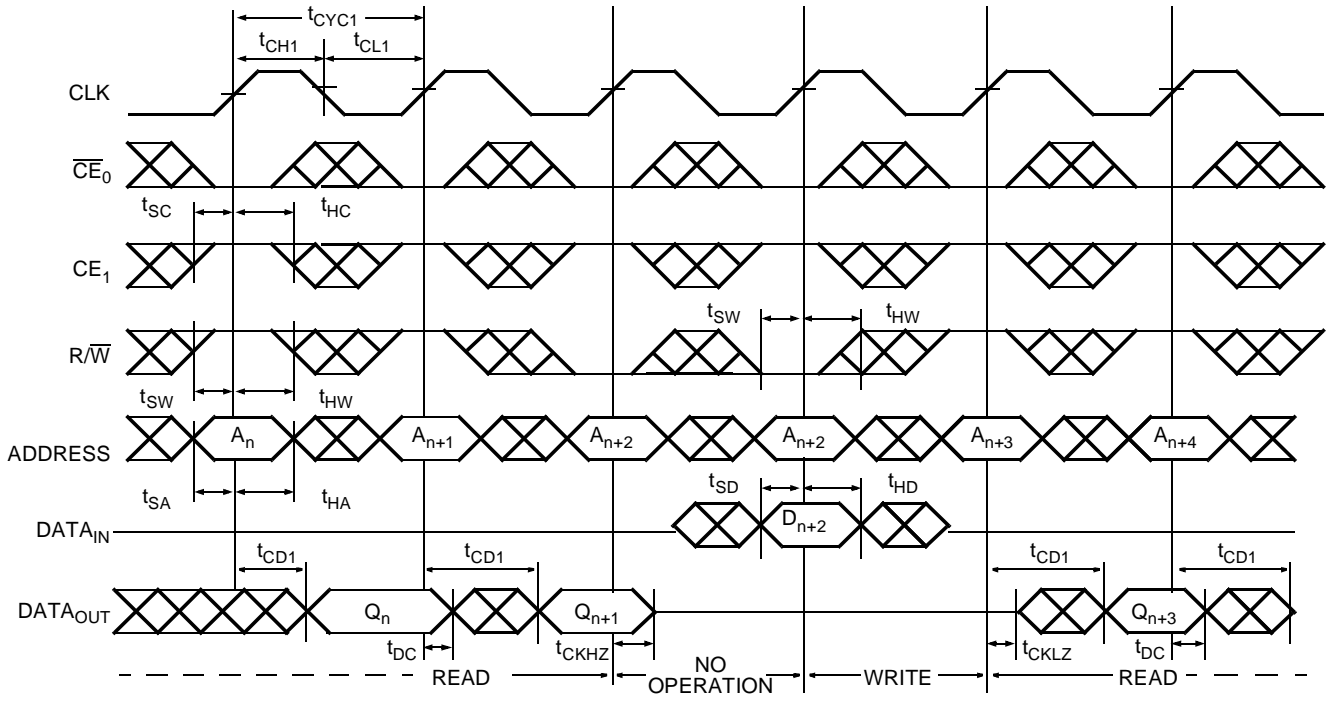
**Flow-Through Read-to-Write-to-Read ($\overline{OE}$ Controlled)**[6,8,12,15]

PRELIMINARY
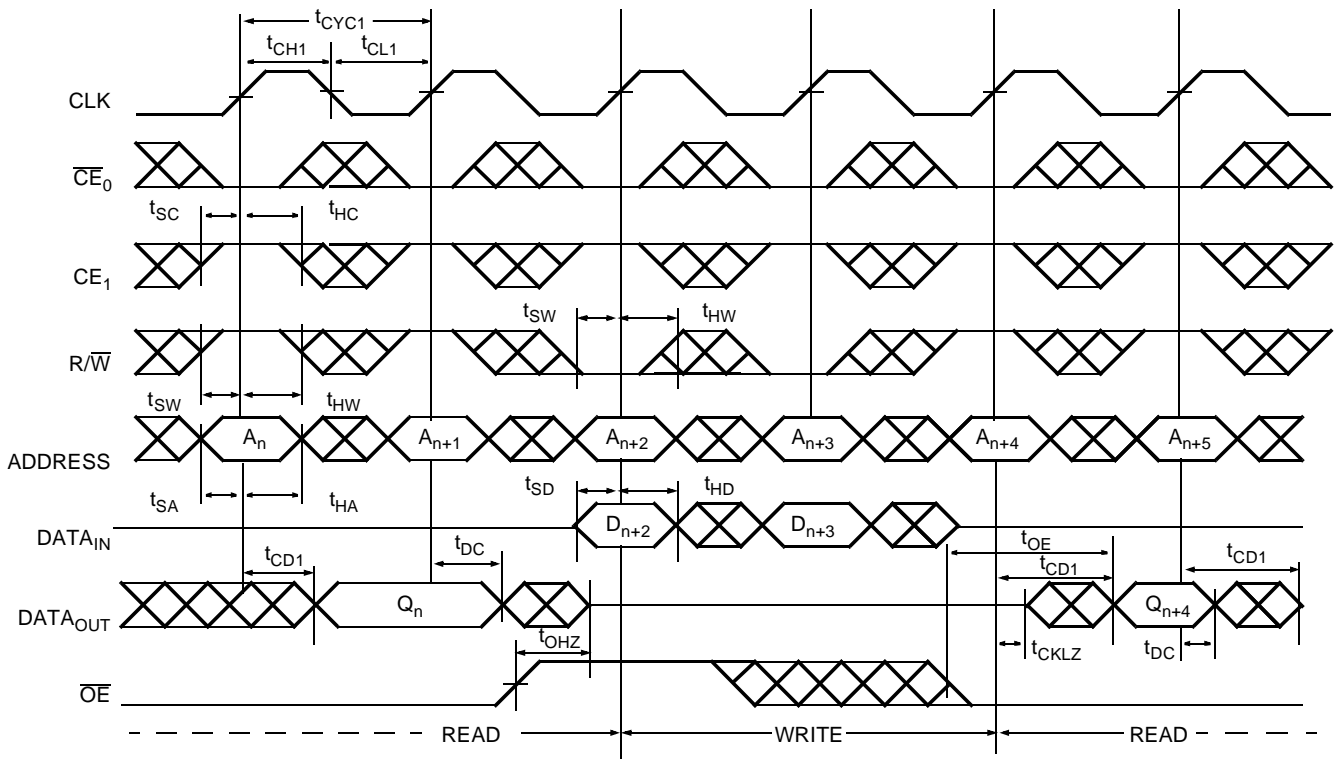
Switching Waveforms (continued)
Pipelined Read with Address Counter Advance[17]
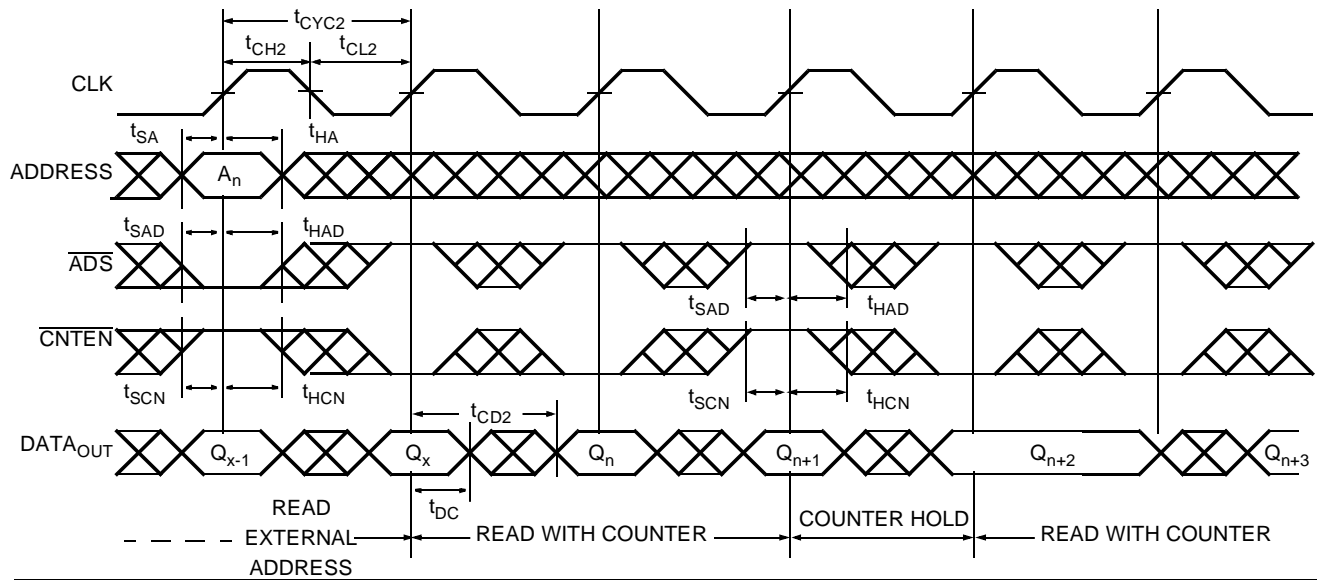
Flow-Through Read with Address Counter Advance[17]

Note:
17. $\overline{CE}_0$ and $\overline{OE} = V_{IL}$; CE_1, $R/\overline{W}$ and $\overline{CNTRST} = V_{IH}$.

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Switching Waveforms (continued)

Write with Address Counter Advance (Flow-Through or Pipelined Outputs)[18,19]

CLK t_{CYC2} t_{CH2} t_{CL2}

ADDRESS t_{SA} A_n t_{HA}

INTERNAL ADDRESS A_n A_{n+1} A_{n+2} A_{n+3} A_{n+4}

$\overline{ADS}$ t_{SAD} t_{HAD}

$\overline{CNTEN}$ t_{SCN} t_{HCN}

DATA$_{IN}$ D_n D_{n+1} D_{n+1} D_{n+2} D_{n+3} D_{n+4} t_{SD} t_{HD}

WRITE EXTERNAL ADDRESS | WRITE WITH COUNTER | WRITE COUNTER HOLD | WRITE WITH COUNTER

Notes:
18. $\overline{CE}_0$ and R/$\overline{W}$ = V_{IL}; CE$_1$ and $\overline{CNTRST}$ = V_{IH}.
19. The "Internal Address" is equal to the "External Address" when $\overline{ADS}$ = V_{IL} and equals the counter output when $\overline{ADS}$ = V_{IH}.

PRELIMINARY

Switching Waveforms (continued)
### Counter Reset (Pipelined Outputs)[8,15,20,21]
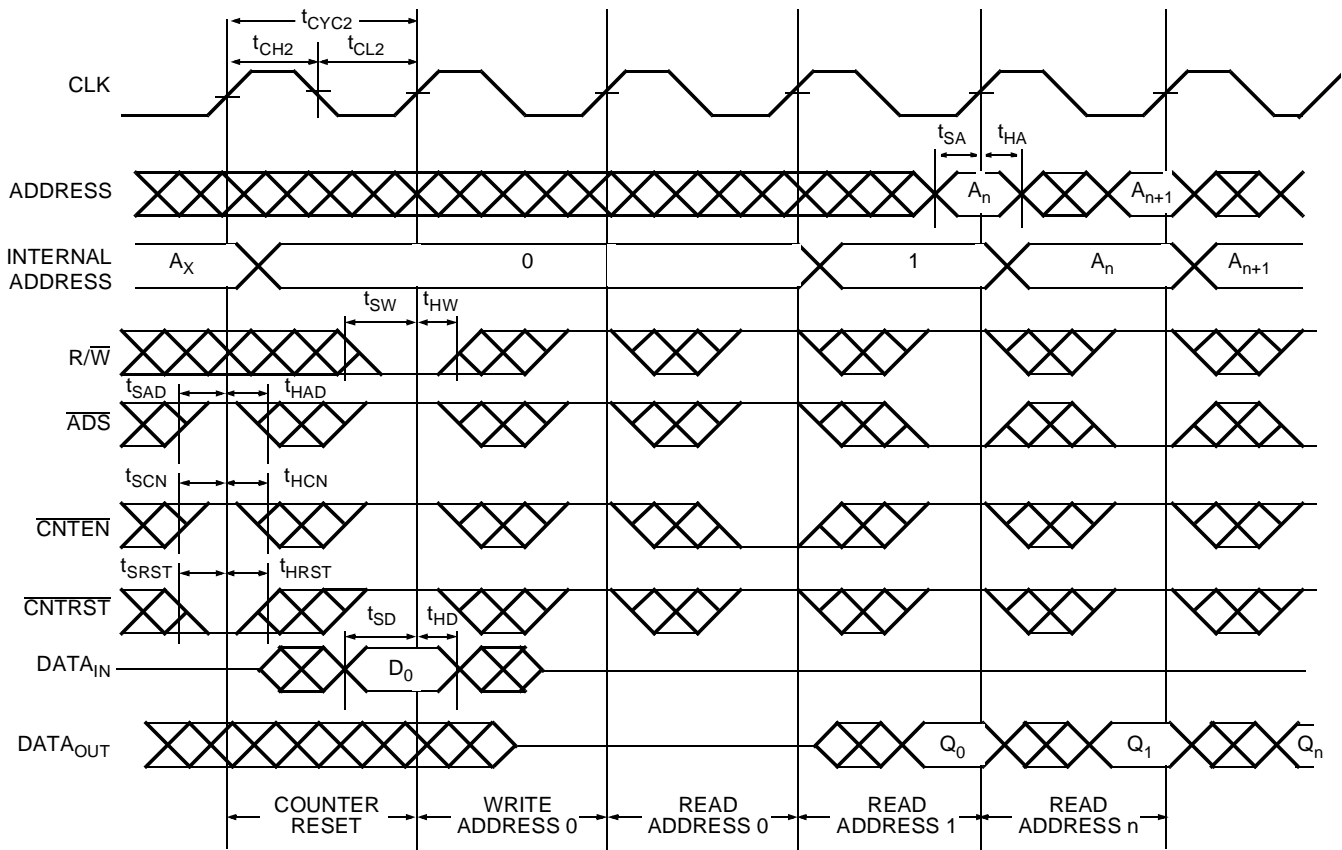
Notes:
20. $\overline{CE}_0 = V_{IL}$; $CE_1 = V_{IH}$.
21. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.

Read/Write and Enable Operation[22,23,24]

Inputs					Outputs	
$\overline{OE}$	CLK	$\overline{CE_0}$	CE_1	$R/\overline{W}$	I/O_0–I/O_8	Operation
X	⌐‾	H	X	X	High-Z	Deselected[25]
X	⌐‾	X	L	X	High-Z	Deselected[25]
X	⌐‾	L	H	L	D_{IN}	Write
L	⌐‾	L	H	H	D_{OUT}	Read[25]
H	X	L	H	X	High-Z	Outputs Disabled

Address Counter Control Operation[22,26,27,28]

Address	Previous Address	CLK	$\overline{ADS}$	$\overline{CNTEN}$	$\overline{CNTRST}$	I/O	Mode	Operation
X	X	⌐‾	X	X	L	$D_{out(0)}$	Reset	Counter Reset to Address 0
A_n	X	⌐‾	L	X	H	$D_{out(n)}$	Load	Address Load into Counter
X	A_n	⌐‾	H	H	H	$D_{out(n)}$	Hold	External Address Blocked—Counter Disabled
X	A_n	⌐‾	H	L	H	$D_{out(n+1)}$	Increment	Counter Enabled—Internal Address Generation

Notes:
22. "X" = Don't Care, "H" = V_{IH}, "L" = V_{IL}.
23. $\overline{ADS}$, $\overline{CNTEN}$, $\overline{CNTRST}$ = Don't Care.
24. $\overline{OE}$ is an asynchronous input signal.
25. When $\overline{CE}$ changes state in the pipelined mode, deselection and read happen in the following clock cycle.
26. $\overline{CE_0}$ and $\overline{OE}$ = V_{IL}; C_{E1} and $R/\overline{W}$ = V_{IH}.
27. Data shown for Flow-through mode; pipelined mode output will be delayed by one cycle.
28. Counter operation is independent of $\overline{CE_0}$ and CE_1.

PRELIMINARY

Ordering Information

8K x9 Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
6.5	CY7C09159-6AC	A100	100-Pin Thin Quad Flat Pack	Commercial
7.5	CY7C09159-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09159-7AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09159-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09159-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

16K x9 Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
6.5	CY7C09169-6AC	A100	100-Pin Thin Quad Flat Pack	Commercial
7.5	CY7C09169-7AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09169-7AI	A100	100-Pin Thin Quad Flat Pack	Industrial
12	CY7C09169-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09169-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

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Package Diagram

100-Pin Thin Quad Flat Pack A100